

OSCILLATORY DEPENDENCE OF ELECTRON  
HALL MOBILITY ON THE ANNEALING  
TEMPERATURE FOR IRRADIATED  
SILICON

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S u m m a r y

Temperature dependences of the electron Hall mobility  $\mu_H$  in *n*-Si single crystals before and after proton irradiation and thermal treatment have been measured. The value of  $\mu_H$  was found to oscillate at a given temperature after the isochronous annealing (IA) at elevating temperatures. The effect is explained as a competition of a dissociation of radiation-induced complex defects and a decay of defect clusters.